

**Amendments to the Specification:**

Please replace the title as follows:

~~METHOD OF FORMING CONDUCTIVE PATTERN SUCH AS ELECTRODE,  
SURFACE EMITTING SEMICONDUCTOR LASER USING THIS METHOD, AND  
MANUFACTURING METHOD FOR THE SAME~~

Please replace the Abstract with the attached substitute Abstract.

Please replace the paragraph beginning on page 1, line 21 to page 2, line 4, with the following rewritten paragraph:

For example, Japanese Laid-Open Patent Application No. 10-154707 discloses a lift-off process. As shown in Figs. 10A to 10E, an upper photoresist layer 15 is formed on a lower photoresist layer 13 and the upper photoresist layer 15 is insolubilized after patterning of two photoresist layers. Then the lower photoresist layer 13 is dissolved to form an undercut for the upper photoresist layer 15n. After that, a conductive film 20(unshown) is formed by the lift-off process. By the formation of the undercut, the needed time for the lift-off process is shortened and the generation of flashes around the conductive layer 20 is prevented.

Please replace the paragraph beginning on page 11, line 9, with the following rewritten paragraph:

Referring to Fig. 4, 1 is a GaAs substrate of n type, 2 is a GaAs buffer layer of n type formed on the substrate 1. 3 is a lower DBR(Distributed Bragg Reflector) layer of n type. 7 is an active region formed on the lower DBR layer 3. The active region 7 is composed of laminated layers, which include an undoped lower spacer layer 4, undoped quantum well layer 5, and undoped upper spacer layer 6. 8 is a current confining layer formed on the active region 7. The current confining layer 8 includes an AlAs portion 8a which defines a circular aperture at the center and includes an oxidized region 8b around the AlAs portion 8a. The

oxidized region 8b confines a current and light which pass through there. 9 is an upper DBR layer of p type formed on the current confining layer 8. 10 is a GaAs contact layer of p type formed on the upper DBR layer 10. 11 is a p-side contact electrode of annular-shape or ring-shape on the contact layer 10, which defines an emission window 11a for the laser light. 12 is a protective film for protecting the emission window 11a, formed on the contact electrode 11. 13 is an interlayer insulating film 13 which covers a top end, side and bottom of the mesa 21. 14 is a p-side wiring electrode, which is formed on the interlayer insulating film 13 and is connected to the contact electrode 11 through a contact hole 13a13a.